

Takahiro Nagata

List of Publications by Year in descending order

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papers

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docs citations

154
times ranked

2530
citing authors

#	ARTICLE	IF	CITATIONS
1	Impact of Cu Electrode on Switching Behavior in a Cu/HfO ₂ /Pt Structure and Resultant Cu Ion Diffusion. Applied Physics Express, 0, 2, 061401.	2.4	106
2	Effect of UV-ozone treatment on electrical properties of PEDOT:PSS film. Organic Electronics, 2011, 12, 279-284.	2.6	77
3	Depletion of the In ₂ O ₃ (001) and (111) surface electron accumulation by an oxygen plasma surface treatment. Applied Physics Letters, 2011, 98, .	3.3	71
4	Electro-optic property of ZnO:X (X=Li,Mg) thin films. Journal of Crystal Growth, 2002, 237-239, 533-537.	1.5	59
5	Prediction of iodide adsorption on oxides by surface complexation modeling with spectroscopic confirmation. Journal of Colloid and Interface Science, 2009, 332, 309-316.	9.4	59
6	Bias application hard x-ray photoelectron spectroscopy study of forming process of Cu/HfO ₂ /Pt resistive random access memory structure. Applied Physics Letters, 2011, 99, .	3.3	56
7	Ferroelectricity of HfxZr1-xO ₂ thin films fabricated by 300°C low temperature process with plasma-enhanced atomic layer deposition. Microelectronic Engineering, 2019, 215, 111013.	2.4	55
8	Highly Uniform Epitaxial ZnO Nanorod Arrays for Nanopiezotronics. Nanoscale Research Letters, 2009, 4, 699-704.	5.7	54
9	Generalized mechanism of the resistance switching in binary-oxide-based resistive random-access memories. Physical Review B, 2013, 87, .	3.2	52
10	Life cycle CO ₂ analysis of LNG and city gas. Applied Energy, 2001, 68, 301-319.	10.1	50
11	Surface structure and chemical states of a-plane and c-plane InN films. Applied Physics Letters, 2009, 95, .	3.3	46
12	Improvement in ferroelectricity of HfxZr1-xO ₂ thin films using top- and bottom-ZrO ₂ nucleation layers. APL Materials, 2019, 7, .	5.1	46
13	Study of the Au Schottky contact formation on oxygen plasma treated n-type SnO ₂ (101) thin films. Journal of Applied Physics, 2010, 107, 033707.	2.5	45
14	Investigations into the Impact of the Template Layer on ZnO Nanowire Arrays Made Using Low Temperature Wet Chemical Growth. Crystal Growth and Design, 2011, 11, 2515-2519.	3.0	41
15	XPS study of Sb-/In-doping and surface pinning effects on the Fermi level in SnO ₂ (101) thin films. Applied Physics Letters, 2011, 98, .	3.3	38
16	XPS and UPS study on band alignment at Pt-Zn-terminated ZnO(0001) interface. Applied Surface Science, 2011, 258, 780-785.	6.1	34
17	Ferroelectricity in Li-Doped ZnO:X Thin Films and their Application in Optical Switching Devices. Japanese Journal of Applied Physics, 2001, 40, 5615-5618.	1.5	33
18	The effects of Xe on an rf plasma and growth of ZnO films by rf sputtering. Journal of Applied Physics, 2004, 95, 3923-3927.	2.5	32

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19	Schottky metal library for ZnO-based UV photodiode fabricated by the combinatorial ion beam-assisted deposition. <i>Applied Surface Science</i> , 2006, 252, 2503-2506.	6.1	31
20	Non-Alloyed Schottky and Ohmic Contacts to As-Grown and Oxygen-Plasma Treated n-Type SnO ₂ (110) and (101) Thin Films. <i>Applied Physics Express</i> , 2009, 2, 106502.	2.4	31
21	Development of AlN/diamond heterojunction field effect transistors. <i>Diamond and Related Materials</i> , 2012, 24, 206-209.	3.9	31
22	Electron transport in semiconducting SnO ₂ : Intentional bulk donors and acceptors, the interface, and the surface. <i>Journal of Materials Research</i> , 2012, 27, 2232-2236.	2.6	26
23	Dual-Heteroatom-Doped Reduced Graphene Oxide Sheets Conjoined CoNi-Based Carbide and Sulfide Nanoparticles for Efficient Oxygen Evolution Reaction. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 40186-40193.	8.0	25
24	Influence of the annealing atmosphere on the structural properties of FePt thin films. <i>Journal of Applied Physics</i> , 2013, 114, .	2.5	22
25	Band-Gap Deformation Potential and Elasticity Limit of Semiconductor Free-Standing Nanorods Characterized <i>in Situ</i> by Scanning Electron Microscope Cathodoluminescence Nanospectroscopy. <i>ACS Nano</i> , 2015, 9, 2989-3001.	14.6	22
26	XPS study on band alignment at Pt-terminated ZnO(0001) interface. <i>Surface and Interface Analysis</i> , 2010, 42, 1528-1531.	1.8	21
27	Hard x-ray photoelectron spectroscopy study on band alignment at poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate)/ZnO interface. <i>Applied Physics Letters</i> , 2012, 101, .	3.3	21
28	Altering properties of cerium oxide thin films by Rh doping. <i>Materials Research Bulletin</i> , 2015, 67, 5-13.	5.2	20
29	Exploring the First High-Entropy Thin Film Libraries: Composition Spread-Controlled Crystalline Structure. <i>ACS Combinatorial Science</i> , 2020, 22, 858-866.	3.8	19
30	Electro-optical effect in ZnO:Mn thin films prepared by Xe sputtering. <i>Journal of Applied Physics</i> , 2006, 99, 013509.	2.5	18
31	Interface structure and the chemical states of Pt film on polar-ZnO single crystal. <i>Applied Physics Letters</i> , 2009, 94, 221904.	3.3	18
32	Electro-Optic Effect in Epitaxial ZnO:Mn Thin Films. <i>Japanese Journal of Applied Physics</i> , 2002, 41, 6916-6918.	1.5	17
33	Systematic investigation of surface and bulk electronic structure of undoped In-polar InN epilayers by hard X-ray photoelectron spectroscopy. <i>Journal of Applied Physics</i> , 2013, 114, .	2.5	17
34	Highly conductive epitaxial ZnO layers deposited by atomic layer deposition. <i>Thin Solid Films</i> , 2014, 562, 485-489.	1.8	17
35	Characteristics of Oxide TFT Using Carbon-Doped In ₂ O ₃ Thin Film Fabricated by Low-Temperature ALD Using Ethylcyclopentadienyl Indium (In-EtCp) and H ₂ O & O ₃ . <i>ECS Transactions</i> , 2019, 92, 3-13.	0.5	17
36	Improvement in ferroelectricity and breakdown voltage of over 20-nm-thick Hf _x Zr _{1-x} O ₂ /ZrO ₂ bilayer by atomic layer deposition. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	17

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37	Composition spread metal thin film fabrication technique based on ion beam sputter deposition. <i>Applied Surface Science</i> , 2006, 252, 2472-2476.	6.1	15
38	Ferroelectric-assisted gold nanoparticles array for centimeter-scale highly reproducible SERS substrates. <i>Scientific Reports</i> , 2017, 7, 3630.	3.3	15
39	Electro-optic effect in ZnO:Mn thin films. <i>Journal of Alloys and Compounds</i> , 2004, 371, 157-159.	5.5	14
40	Fully engineered homoepitaxial zinc oxide nanopillar array for near-surface light wave manipulation. <i>Applied Physics Letters</i> , 2008, 92, 183114.	3.3	14
41	Epitaxial growth of nonpolar ZnO and n-ZnO/i-ZnO/p-GaN heterostructure on Si(001) for ultraviolet light emitting diodes. <i>Applied Physics Express</i> , 2014, 7, 062102.	2.4	14
42	Effect of Annealing on Implanted Ga of Diamond-Like Carbon Thin Films Fabricated by Focused-Ion-Beam Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 9010-9012.	1.5	13
43	Arbitrary cross-section SEM-cathodoluminescence imaging of growth sectors and local carrier concentrations within micro-sampled semiconductor nanorods. <i>Nature Communications</i> , 2016, 7, 10609.	12.8	13
44	GaN nanostructure fabrication by focused-ion-beam-assisted chemical vapor deposition. <i>Applied Physics Letters</i> , 2005, 87, 013103.	3.3	12
45	Composition-spread thin films of pentacene and 6,13-pentacenequinone fabricated by using continuous-wave laser molecular beam epitaxy. <i>Applied Surface Science</i> , 2008, 254, 2336-2341.	6.1	12
46	Thermal stability of Ni silicide films on heavily doped n+ and p+ Si substrates. <i>Microelectronic Engineering</i> , 2008, 85, 1642-1646.	2.4	12
47	Nanoimprint for Fabrication of Highly Ordered Epitaxial ZnO Nanorods on Transparent Conductive Oxide Films. <i>Applied Physics Express</i> , 2012, 5, 095003.	2.4	12
48	Photoinduced Phase Transformations in Boron Nitride: New Polytypic Forms of sp ³ -Bonded (6H- and 30H-) BN. <i>Journal of Physical Chemistry C</i> , 2010, 114, 13176-13186.	3.1	11
49	Chemical Synthesis of Multilayered Nanostructured Perovskite Thin Films with Dielectric Features for Electric Capacitors. <i>ACS Applied Nano Materials</i> , 2018, 1, 915-921.	5.0	11
50	Elobixibat, an ileal bile acid transporter inhibitor, ameliorates non-alcoholic steatohepatitis in mice. <i>Hepatology International</i> , 2021, 15, 392-404.	4.2	11
51	Evidence-based recommender system for high-entropy alloys. <i>Nature Computational Science</i> , 2021, 1, 470-478.	8.0	11
52	Dissipation-factor-based criterion for the validity of carrier-type identification by capacitance-voltage measurements. <i>Applied Physics Letters</i> , 2009, 94, 152110.	3.3	10
53	Improving the performance of inorganic-organic hybrid photovoltaic devices by uniform ordering of ZnO nanorods and near-atmospheric pressure nitrogen plasma treatment. <i>Journal of Applied Physics</i> , 2013, 113, 083708.	2.5	10
54	Molecular magnetic thin films made from Ni-Co Prussian blue analogue anchored on silicon wafers. <i>Journal of Magnetism and Magnetic Materials</i> , 2019, 486, 165276.	2.3	10

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55	Valence Band Modification of a (Ga _x In _{1-x}) ₂ O ₃ Solid Solution System Fabricated by Combinatorial Synthesis. ACS Combinatorial Science, 2020, 22, 433-439.	3.8	10
56	Plasma-assisted molecular beam epitaxy of SnO(001) films: Metastability, hole transport properties, Seebeck coefficient, and effective hole mass. Physical Review Materials, 2020, 4, .	2.4	10
57	BaTiO ₃ based relaxor ferroelectric epitaxial thin-films for high-temperature operational capacitors. Japanese Journal of Applied Physics, 2015, 54, 04DH02.	1.5	9
58	Photoelectron spectroscopic study of electronic state and surface structure of In ₂ O ₃ single crystals. Applied Physics Express, 2017, 10, 011102.	2.4	9
59	Ferroelectricity of Hf _x Zr _{1-x} O ₂ Thin Films Fabricated Using TiN Stressor and ZrO ₂ Nucleation Techniques. ECS Transactions, 2018, 86, 31-38.	0.5	9
60	Gold nanoparticles anchored on mesoporous zirconia thin films for efficient catalytic oxidation of carbon monoxide at low temperatures. Microporous and Mesoporous Materials, 2019, 288, 109530.	4.4	9
61	Correlation between ferroelectricity and ferroelectric orthorhombic phase of Hf _x Zr _{1-x} O ₂ thin films using synchrotron x-ray analysis. APL Materials, 2021, 9, .	5.1	9
62	Improvement of Ferroelectricity and Fatigue Property of Thicker Hf _x Zr _{1-x} O ₂ /ZrO ₂ Bi-layer. ECS Transactions, 2020, 98, 63-70.	0.5	9
63	Impact of Mg concentration on energy-band-depth profile of Mg-doped InN epilayers analyzed by hard X-ray photoelectron spectroscopy. Applied Physics Letters, 2013, 103, .	3.3	8
64	Resolving lateral and vertical structures by ellipsometry using wavelength range scan. Thin Solid Films, 2014, 571, 579-583.	1.8	8
65	Ge incorporated epitaxy of (110) rutile TiO ₂ on (100) Ge single crystal at low temperature by pulsed laser deposition. Thin Solid Films, 2015, 591, 105-110.	1.8	8
66	Effects of substrate self-bias and nitrogen flow rate on non-polar AlN film growth by reactive sputtering. Japanese Journal of Applied Physics, 2019, 58, SDDG07.	1.5	8
67	Mesostructured HfO ₂ /Al ₂ O ₃ Composite Thin Films with Reduced Leakage Current for Ion-Conducting Devices. ACS Omega, 2019, 4, 14680-14687.	3.5	8
68	Optical propagation loss of ZnO films grown on sapphire. Journal of Applied Physics, 2004, 95, 1673-1676.	2.5	7
69	Observation of filament formation process of Cu/HfO ₂ /Pt ReRAM structure by hard x-ray photoelectron spectroscopy under bias operation. Journal of Materials Research, 2012, 27, 869-878.	2.6	7
70	Photoelectron spectroscopic study of electronic states and surface structure of an in situ cleaved In ₂ O ₃ (111) single crystal. Japanese Journal of Applied Physics, 2019, 58, SDDG06.	1.5	7
71	P-type sp ³ -bonded BN/n-type Si heterodiode solar cell fabricated by laser-plasma synchronous CVD method. Journal Physics D: Applied Physics, 2009, 42, 225107.	2.8	6
72	Schottky barrier height behavior of Pt-Ru alloy contacts on single-crystal n-ZnO. Journal of Applied Physics, 2010, 107, .	2.5	6

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73	Epitaxial growth of high dielectric constant lead-free relaxor ferroelectric for high-temperature operational film capacitor. <i>Thin Solid Films</i> , 2015, 592, 29-33.	1.8	6
74	Photoelectron spectroscopic study on electronic state and electrical properties of SnO ₂ single crystals. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 080903.	1.5	6
75	Comparison of characteristics of thin-film transistor with In ₂ O ₃ and carbon-doped In ₂ O ₃ channels by atomic layer deposition and post-metallization annealing in O ₃ . <i>Japanese Journal of Applied Physics</i> , 2021, 60, 030903.	1.5	6
76	Surface Nitridation of c-Plane Sapphire Substrate by Near-Atmospheric Nitrogen Plasma. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 040206.	1.5	5
77	Combinatorial Synthesis of Cu/(Ta _x Nb _{1-x}) ₂ O ₅ Stack Structure for Nanoionics-Type ReRAM Device. <i>ACS Combinatorial Science</i> , 2013, 15, 435-438.	3.8	5
78	Photoelectron spectroscopic study on monolayer pentacene thin-film/polar ZnO single-crystal hybrid interface. <i>Applied Physics Express</i> , 2017, 10, 025702.	2.4	5
79	Surface and bulk electronic structures of heavily Mg-doped InN epilayer by hard X-ray photoelectron spectroscopy. <i>Journal of Applied Physics</i> , 2017, 121, .	2.5	5
80	The electrical conductivity of cubic (In _{1-x} Ga _x) ₂ O ₃ films (x ≈ 0.18): native bulk point defects, Sn-doping, and the surface electron accumulation layer. <i>Japanese Journal of Applied Physics</i> , 2022, 61, 045502.	1.5	5
81	Molecular beam epitaxy of single-crystalline bixbyite $\text{In}_{2-x}\text{Ga}_x\text{O}_3$. <i>Physical Review Materials</i> , 2022, 6, .	2.4	5
82	Crystal Structures of Pt-Ru Alloy Schottky Contacts on ZnO by Combinatorial Ion Beam Deposition. <i>Japanese Journal of Applied Physics</i> , 2007, 46, 2907-2909.	1.5	4
83	GaN Film Fabrication by Near-Atmospheric Plasma-Assisted Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 2007, 46, L43-L45.	1.5	4
84	Reduction of interfacial SiO ₂ at HfO ₂ /Si interface with Ta ₂ O ₅ cap. <i>Journal of Applied Physics</i> , 2013, 114, .	2.5	4
85	Combinatorial synthesis of BaTiO ₃ -Bi(Mg ₂ /3Nb ₁ /3)O ₃ thin-films for high-temperature capacitors. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 06FJ02.	1.5	4
86	Crystallographic polarity effect of ZnO on thin film growth of pentacene. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 04CJ03.	1.5	4
87	Reliability of Al ₂ O ₃ /In-Si-O-C Thin-Film Transistors with an Al ₂ O ₃ Passivation Layer under Gate-Bias Stress. <i>ECS Transactions</i> , 2018, 86, 135-145.	0.5	4
88	Relationship between band-offset, gate leakage current, and interface states density at SiO ₂ /4H-SiC (000-1) interface. <i>AIP Advances</i> , 2019, 9, 045002.	1.3	4
89	Indium oxide. , 2019, , 523-546.		4
90	Photoelectron spectroscopic study on electronic state of corundum In ₂ O ₃ epitaxial thin film grown by mist-CVD. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SIIG12.	1.5	4

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91	Effects of low temperature buffer layer on all-sputtered epitaxial GaN/AlN film on Si (111) substrate. Japanese Journal of Applied Physics, 2021, 60, SCCG03.	1.5	4
92	Observation of second harmonic electron cyclotron resonance heating and current-drive transition during non-inductive plasma start-up experiment in QUEST. Plasma Physics and Controlled Fusion, 2021, 63, 105002.	2.1	4
93	Low-temperature growth of GaN microcrystals from position-controlled Ga droplets arrayed by a low-energy focused ion beam system. Journal of Crystal Growth, 2005, 283, 328-331.	1.5	3
94	Effects of Single-Crystalline GaN Target on GaN Thin Films in Pulsed Laser Deposition Process. Japanese Journal of Applied Physics, 2005, 44, 7896-7900.	1.5	3
95	Photoelectron spectroscopic study on band alignment of poly(3-hexylthiophene-2,5-diyl)/polar-ZnO heterointerface. Thin Solid Films, 2014, 554, 194-198.	1.8	3
96	Heteroepitaxial growth of nonpolar Cu-doped ZnO thin film on MnS-buffered (100) Si substrate. Japanese Journal of Applied Physics, 2015, 54, 06FJ10.	1.5	3
97	Bias induced Cu ion migration behavior in resistive change memory structure observed by hard X-ray photoelectron spectroscopy. Japanese Journal of Applied Physics, 2015, 54, 06FG01.	1.5	3
98	Effect of Y and Mn doping into rutile type TiO ₂ /Ge stack structure by combinatorial synthesis. Japanese Journal of Applied Physics, 2017, 56, 06GF11.	1.5	3
99	HFS Injection of X-Mode for EBW Conversion in QUEST. Plasma and Fusion Research, 2019, 14, 1205038-1205038.	0.7	3
100	Crystal growth of a MnS buffer layer for non-polar AlN on Si (100) deposited by radio frequency magnetron sputtering. Japanese Journal of Applied Physics, 2019, 58, SBBK03.	1.5	3
101	Influence of adsorbed oxygen concentration on characteristics of carbon-doped indium oxide thin-film transistors under bias stress. Japanese Journal of Applied Physics, 2021, 60, SCCM01.	1.5	3
102	Bandgap widening and behavior of Raman-active phonon modes of cubic single-crystalline (In,Ga)2O ₃ alloy films. Applied Physics Letters, 2021, 119, .	3.3	3
103	Validation with Measured Data of Photoelectron Yield Spectroscopy (PYS) Threshold Using Machine Learning. Vacuum and Surface Science, 2019, 62, 504-510.	0.1	3
104	Characterization of Deposited Materials Formed by Focused Ion Beam-Induced Chemical Vapor Deposition Using AuSi Alloyed Metal Source. Japanese Journal of Applied Physics, 2008, 47, 5018-5021.	1.5	2
105	Electrical properties and stability of an epitaxial alumina film formed on Cu-9 at.% Al(111). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, 021509.	2.1	2
106	Effect of near atmospheric pressure nitrogen plasma treatment on Pt/ZnO interface. Journal of Applied Physics, 2012, 112, .	2.5	2
107	Thin-film growth of (110) rutile TiO ₂ on (100) Ge substrate by pulsed laser deposition. Japanese Journal of Applied Physics, 2016, 55, 06GG06.	1.5	2
108	Contacting ZnO Individual Crystal Facets by Direct Write Lithography. ACS Applied Materials & Interfaces, 2016, 8, 23891-23898.	8.0	2

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109	Spectroscopic Observation of the Interface States at the SiO ₂ /4H-SiC(0001) Interface. E-Journal of Surface Science and Nanotechnology, 2019, 17, 56-60.	0.4	2
110	Band alignment at non-polar AlN/MnS interface investigated by hard X-ray photoelectron spectroscopy. Japanese Journal of Applied Physics, 2020, 59, SIIG07.	1.5	2
111	Accelerating two-dimensional X-ray diffraction measurement and analysis with density-based clustering for thin films. Japanese Journal of Applied Physics, 2021, 60, SCCG04.	1.5	2
112	Initial Results from High-Field-Side Transient CHI Start-Up on QUEST. Plasma and Fusion Research, 2021, 16, 2402048-2402048.	0.7	2
113	Automatic Threshold Prediction of Photoelectron Yield Spectroscopy (PYS) by Machine Learning. Vacuum and Surface Science, 2020, 63, 270-276.	0.1	2
114	Effect of Annealing on Mechanical Properties of Materials Formed by Focused Au or Si Ion-Beam-Induced Chemical Vapor Deposition Using Phenanthrene. Japanese Journal of Applied Physics, 2009, 48, 06FB03.	1.5	1
115	Bottom-electrode effect on switching behavior and interface reaction in nanoionic-based resistive changing memory. Japanese Journal of Applied Physics, 2016, 55, 08PC03.	1.5	1
116	Screening charge localization at LiNbO ₃ surface with Schottky junction. Applied Physics Letters, 2016, 108, .	3.3	1
117	Tooth Root Bending Stress Analysis of Pre-alloyed Sintered Steel Gears with Different Densities using FEM Model Considering Voids. Funtai Oyobi Fumatsu Yakin/Journal of the Japan Society of Powder and Powder Metallurgy, 2016, 63, 568-572.	0.2	1
118	Surface and bulk electronic structures of unintentionally and Mg-doped In _{0.7} Ga _{0.3} N epilayer by hard X-ray photoelectron spectroscopy. Journal of Applied Physics, 2018, 123, 095701.	2.5	1
119	Combinatorial Thin Film Synthesis for Developments of New High Dielectric Constant Thin Film Materials. Transactions of the Materials Research Society of Japan, 2018, 43, 249-254.	0.2	1
120	Measurement of Dynamic Retention with Fast Ejecting System of Targeted Sample (FESTA). Plasma and Fusion Research, 2020, 15, 2402013-2402013.	0.7	1
121	Interface stability of electrode/Bi-containing relaxor ferroelectric oxide for high-temperature operational capacitor. Japanese Journal of Applied Physics, 2016, 55, 06GJ12.	1.5	1
122	Auger Depth Profiling Analysis of HfO ₂ /Si Specimen Using an Ultra Low Angle Incidence Ion Beam. Journal of Surface Analysis (Online), 2018, 24, 192-205.	0.1	1
123	(Invited) Development of New High-Dielectric Constant Thin Films By Combinatorial Synthesis. ECS Transactions, 2020, 97, 61-66.	0.5	1
124	Effect of reactive gas condition on nonpolar AlN film growth on MnS/Si (100) by reactive DC sputtering. Japanese Journal of Applied Physics, 0, , .	1.5	1
125	Direct feature extraction from two-dimensional X-ray diffraction images of semiconductor thin films for fabrication analysis. Science and Technology of Advanced Materials Methods, 2022, 2, 23-37.	1.3	1
126	Operando hard X-ray photoelectron spectroscopy study of buried interface chemistry of Au/In _{0.16} Co _{0.04} /Al ₂ O ₃ /p<math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" id="d1e383" altimg="si20.svg">$+$</math>-Si stacks. Applied Surface Science, 2022, 593, 153272.	6.1	1

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127	(Invited) Combinatorial Synthesis and Interface Analysis for Development of High Dielectric Constant Thin Films. ECS Transactions, 2022, 108, 61-68.	0.5	1
128	Polarity Control of an All-Sputtered Epitaxial GaN/AlN/Al Film on a Si(111) Substrate by Intermediate Oxidization. ACS Omega, 2022, 7, 19380-19387.	3.5	1
129	Position Controlled GaN Nano-Structures Fabricated by Low Energy Focused Ion Beam System.. Materials Research Society Symposia Proceedings, 2003, 792, 621.	0.1	0
130	Ni silicidation on heavily doped Si substrates. , 2008, , .		0
131	New Phases of sp ³ -bonded Boron Nitride Prepared by Photo-Assisted Plasma Processing Methods: The Fundamentals and Applications to Electronic Devices. , 2011, , .		0
132	(Invited) Photoelectron Spectroscopic Study on High-k Dielectrics Based Nanoionics-Type ReRAM Structure under Bias Operation. ECS Transactions, 2014, 61, 301-310.	0.5	0
133	Interfacial charge transfer behavior of conducting polymers as contact electrode for semiconductor devices. Japanese Journal of Applied Physics, 2016, 55, 04EC10.	1.5	0
134	Direct Observation of Energy Distribution of Interface States at SiO ₂ /4H-SiC Interface. ECS Transactions, 2016, 75, 207-211.	0.5	0
135	Hard X-Ray Photoelectron Spectroscopic Study on High-k Dielectrics Based Resistive Random Access Memory. ECS Transactions, 2017, 75, 39-47.	0.5	0
136	Study of Sn and Mg doping effects on TiO ₂ /Ge stack structure by combinatorial synthesis. Japanese Journal of Applied Physics, 2018, 57, 04FJ04.	1.5	0
137	Photoelectroscopic Study of Mn Barrier Layer on SiO ₂ for Si Wafer Bonding Process. , 2019, , .		0
138	Temperature and polarity dependence of electrical properties of ZnO film on pyroelectric LiNbO ₃ single crystal. Japanese Journal of Applied Physics, 2020, 59, SIIG11.	1.5	0
139	Effects of Zn _x Mn _{1-x} S buffer layer on nonpolar AlN growth on Si (100) substrate. Japanese Journal of Applied Physics, 2021, 60, SCCG02.	1.5	0
140	Kerr effect microscope combined with a pulse magnet to observe high-entropy alloys fabricated using combinatorial technology. Science and Technology of Advanced Materials Methods, 0, , .	1.3	0
141	Bias-application in Hard X-ray Photoelectronic Study for Advanced Materials. Hyomen Kagaku, 2011, 32, 320-324.	0.0	0
142	Charge-Transfer Behavior of Conducting Polymers as Contact Electrode for Semiconductor Devices. , 2014, , .		0
143	Interfacial Charge Transfer Behaviour of Conducting Polymers as Contact Electrode for Semiconductor Devices. , 2015, , .		0
144	Direct Observation of the Energy Distribution of Interface States at SiO ₂ /4H-SiC Interface: Operando Hard X-ray Photoelectron Spectroscopic Study. Hyomen Kagaku, 2017, 38, 347-350.	0.0	0

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145	Combinatorial Thin-Film Synthesis for New Nanoelectronics Materials. NIMS Monographs, 2020, , 75-87.	0.3	0
146	Switching Control of Oxide-Based Resistive Random-Access Memory by Valence State Control of Oxide. NIMS Monographs, 2020, , 69-74.	0.3	0
147	Changes in Schottky Barrier Height Behavior of Pt-Ru Alloy Contacts on Single-Crystal ZnO. NIMS Monographs, 2020, , 5-26.	0.3	0
148	Surface Passivation Effect on Schottky Contact Formation of Oxide Semiconductors. NIMS Monographs, 2020, , 27-39.	0.3	0
149	Bias-Induced Interfacial Redox Reaction in Oxide-Based Resistive Random-Access Memory Structure. NIMS Monographs, 2020, , 41-67.	0.3	0
150	Development of the Material Sequencer for Automatic Various Evaluations. Journal of Surface Analysis (Online), 2021, 28, 35-45.	0.1	0
151	(Invited) Combinatorial Synthesis and Interface Analysis for Development of High Dielectric Constant Thin Films. ECS Meeting Abstracts, 2022, MA2022-01, 1070-1070.	0.0	0